

REPLACEMENT SHEET FOR ABSTRACT

A semiconductor device may include a substrate, an insulating layer formed on the substrate and a conductive fin formed on the insulating layer. The conductive fin may include a number of side surfaces and a top surface. The semiconductor device may also include a source region formed on the insulating layer adjacent a first end of the conductive fin and a drain region formed on the insulating layer adjacent a second end of the conductive fin. The semiconductor device may further include a metal gate formed on the insulating layer adjacent the conductive fin in a channel region of the semiconductor device.